2.7 Photo-Resist/Polyimide Etch (Anisotropic)

Mode: Reactive Ion Etch (RIE)
Pumps: Turbo
Susceptor Material: Graphite or Ardel
Temperature (°C): 25

Electrode Size: 6" 8" 11"

Gases (sccm):
O₂  5  8  10
He  5  8  10

Pressure (mTorr): 10 10 10
Power (Watts): 150 175 200
DC-bias (Volts): 500 500 500

Typical Etch Rate (Å/min.): 1000

Notes:
Optimum performance is obtained using a silicon dioxide mask. Metal masks can cause "grass" to form in the bottom of the etched features due to re-deposition of the mask material. The He is necessary in order to obtain a high degree of anisotropy; if this is not essential, the He can be omitted, with a resultant increase in the etch rate.